ABSTRACT OF THE DISCLOSURE

On an Si substrate **1**, a buffer layer **2**, a SiGe layer **3**, and an Si cap layer **4** are formed. A mask is formed on the substrate, and then the substrate is patterned. In this manner, a trench **7a** is formed so as to reach the Si substrate **1** and have the side faces of the SiGe layer **3** exposed. Then, the surface of the trench **7a** is subjected to heat treatment for one hour at 750 ℃ so that Ge contained in a surface portion of the SiGe layer **3** is evaporated. Thus, a Ge evaporated portion **8** having a lower Ge content than that of other part of the SiGe layer **3** is formed in part of the SiGe layer **3** exposed at part of the trench **7a**. Thereafter, the walls of the trench **7a** are oxidized.